



Science & Technology
Facilities Council

Serial Powering System Architecture

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STFC Rutherford Appleton Laboratory

On behalf of the SP Community

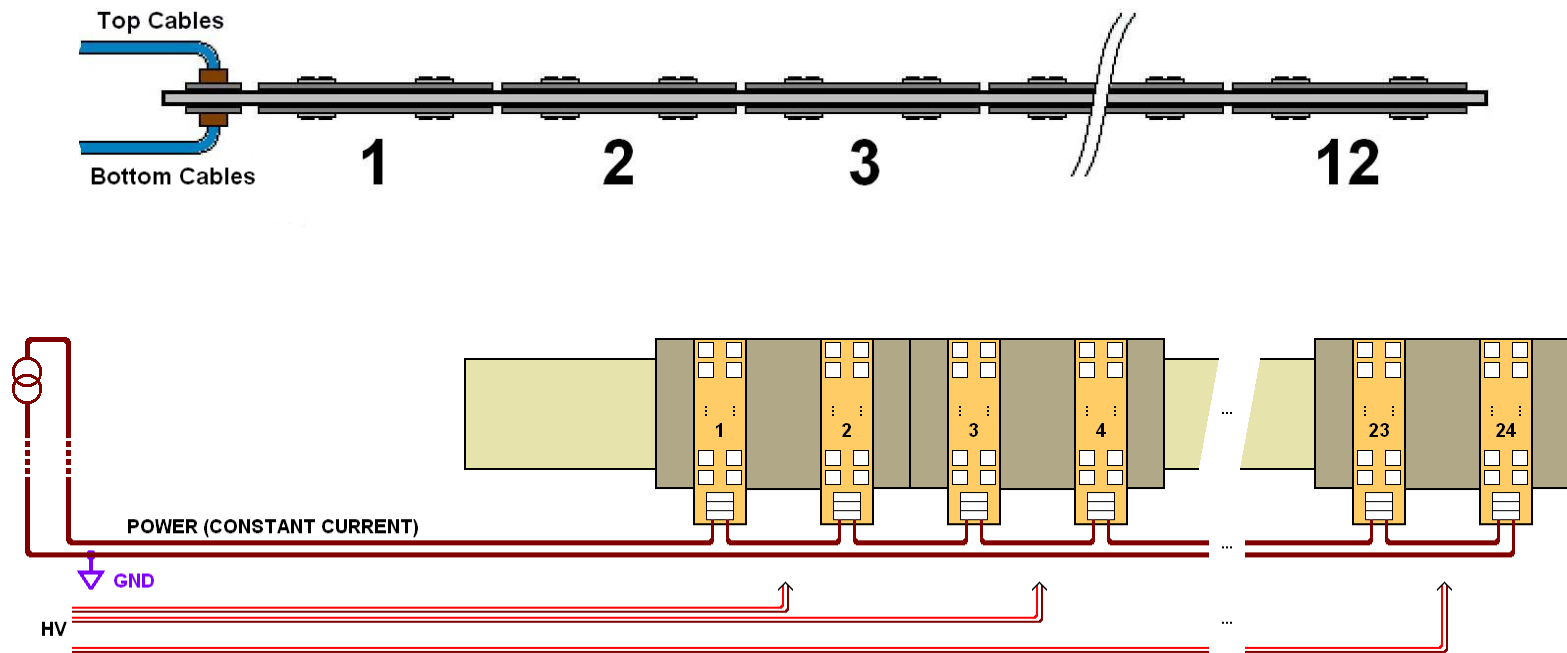
Acknowledgement: many figures prepared by Richard Holt, RAL

Outline

- SP Architecture: Modules and Staves
- System Tests
- Shunt Architectures
- Efficiency, DC-DC and 130nm
- SP and endcap geometries
- AC coupled (M)LVDS
- Serial Powering and HV
- Protection Schemes
- First Results from ABCN Integrated Shunts
- Summary and Next Steps



SP Stave Architecture



SP Stave Architecture

For strips, the stave comprises two separate planes:

- The top and bottom faces have separate current loops
- The grounds of the two faces are connected at the stave end

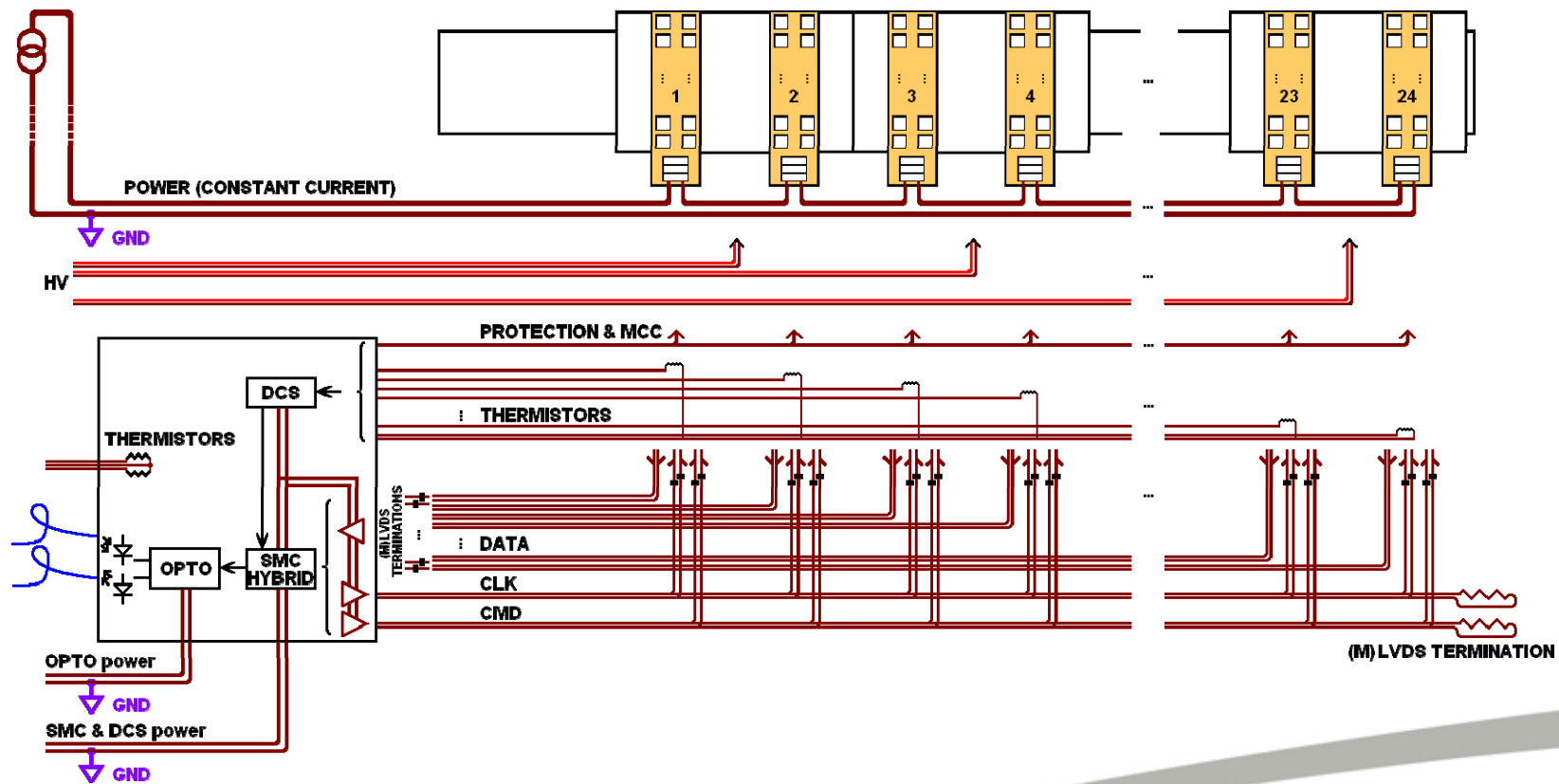
Features common with pixels:

- CLK and COM are AC coupled on each hybrid
- DATA is AC coupled at the stave end
- Protection can be included such that one failed hybrid does not disturb the remainder
- DCS can monitor hybrid temperatures, the shunt current and (ideally) hybrid voltages

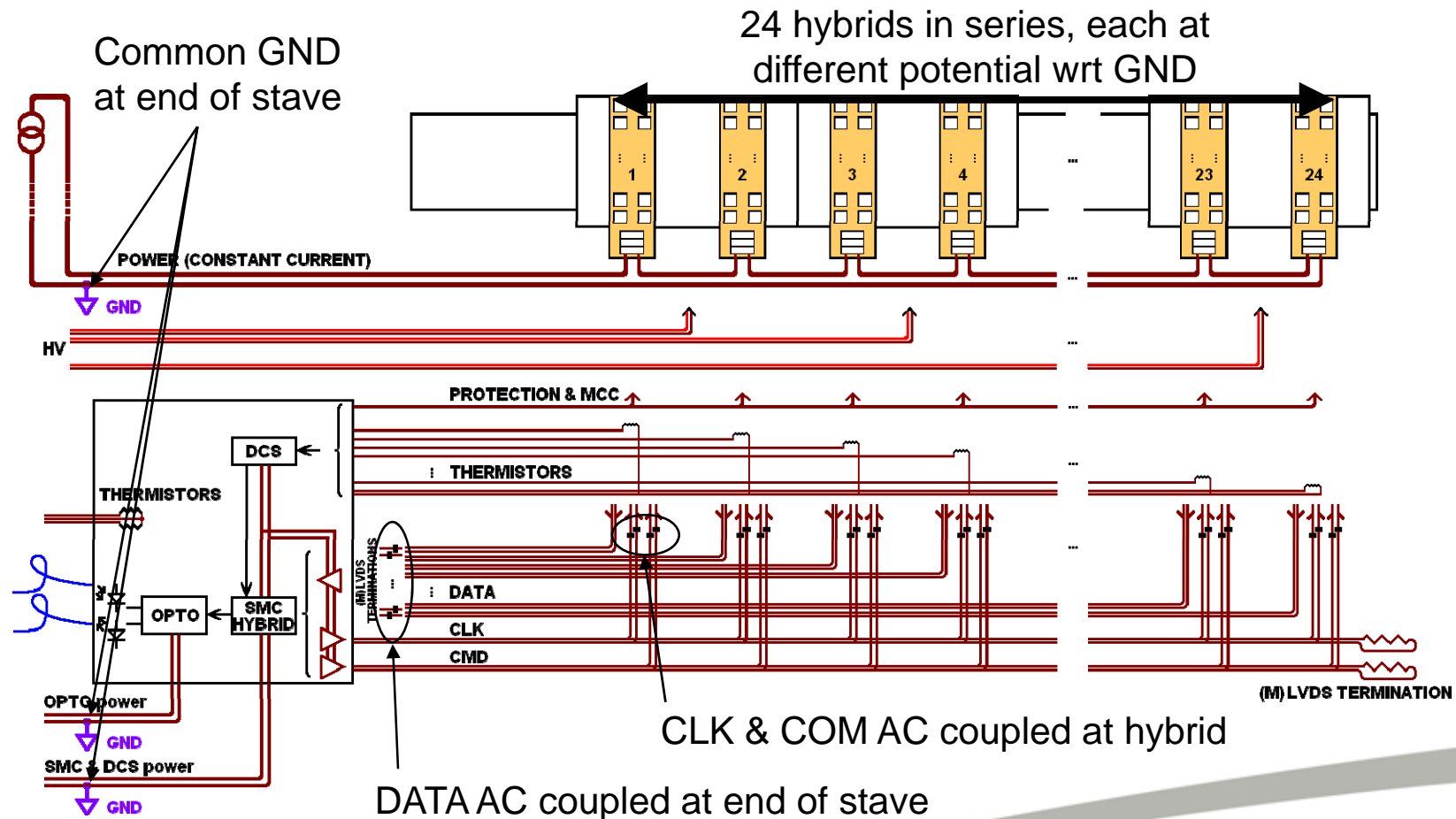
Depending upon design choices, the total voltage across each serial powering loop can be as low as 24 x 1V for strips, less for pixels (shorter stave)...



SP Stave Architecture



SP Stave Architecture



(DC-DC powered stave would look similar, apart from the absence of AC coupled IO)

SP Module Architecture

Module Controller Chip (MCC)

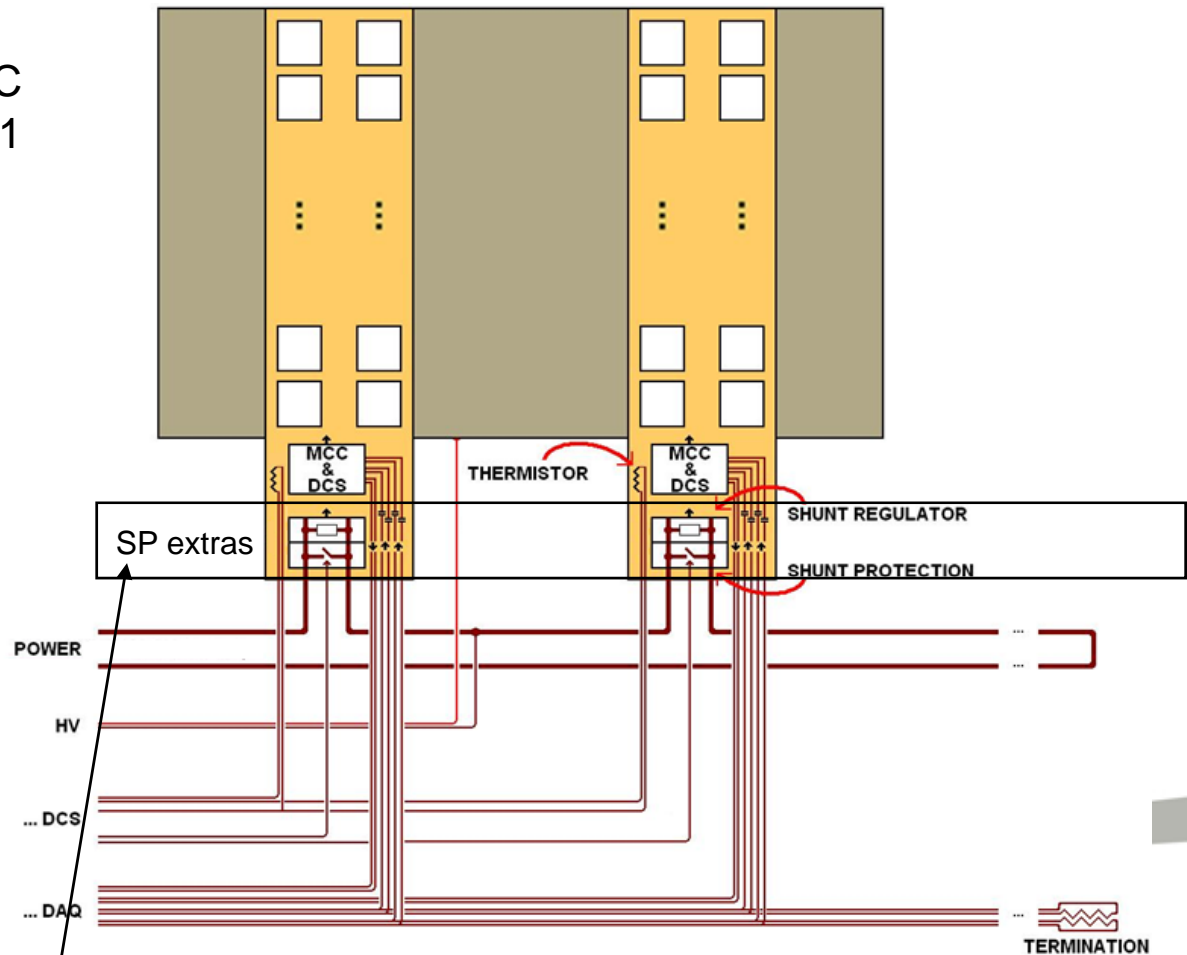
- Functions common to SP & DC-DC
 - multiplexes 2 data streams into 1
 - voltage monitoring
- Additional for SP
 - powered by SP
 - AC coupling of CLK & COM
 - Requires 4 capacitors
 - Everything else on chip

Temperature

- read by (stave end) DCS
 - Monitor T before power applied

Shunt protection

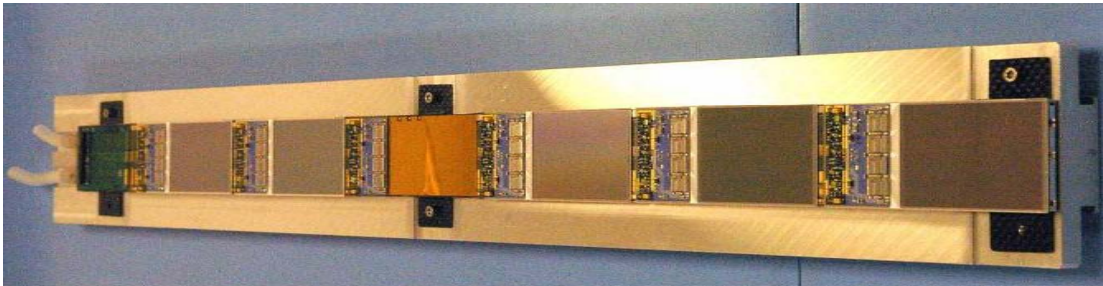
- under DCS control
 - Turn on modules independently



System tests of SP staves

1) Pixel stave with FE-I3 (old, published)

2) Stave06: 6 module stave with ABCD



We have verified that:

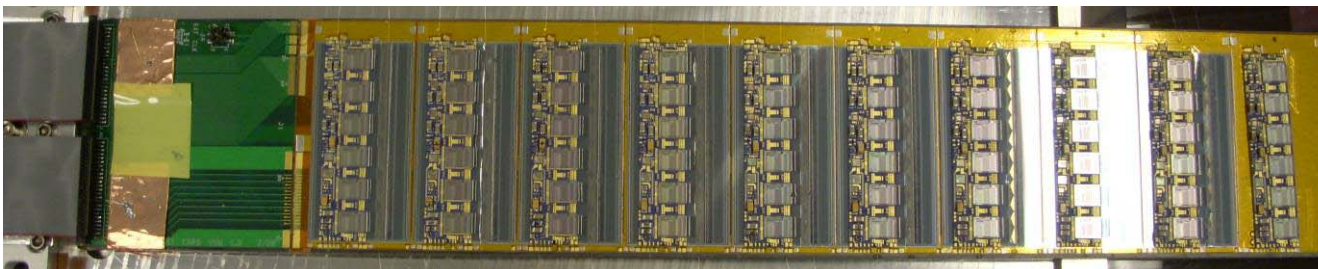
1. Noise is not an issue
2. AC coupled (M)LVDS works
3. SP uses little extra real estate
4. Can use single HV line / strip stave

All staves working well!

$$30 * 4V = 120V$$

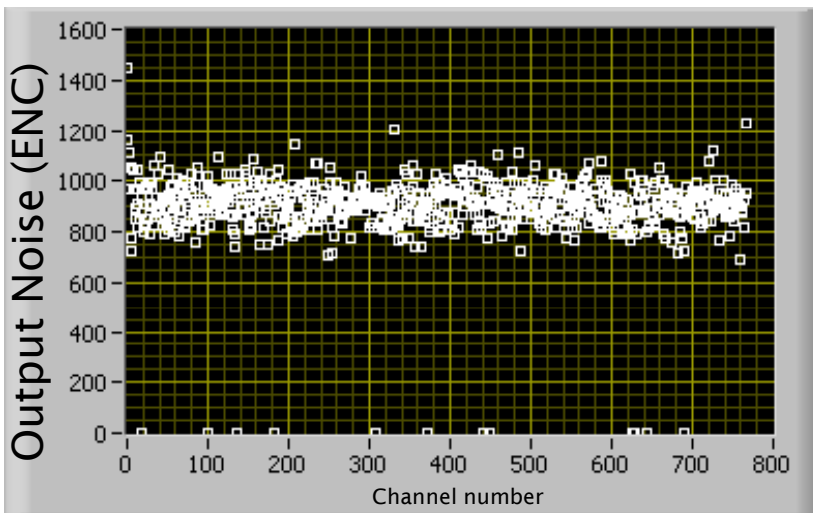
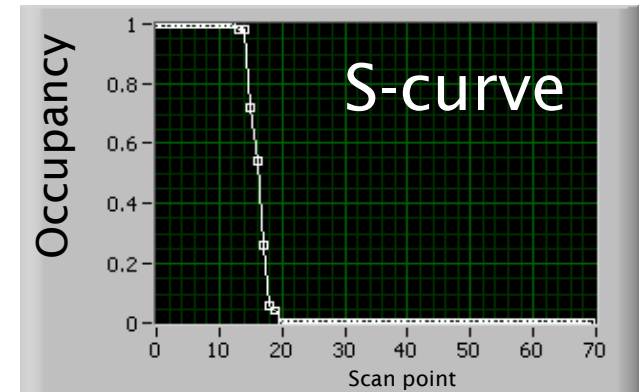
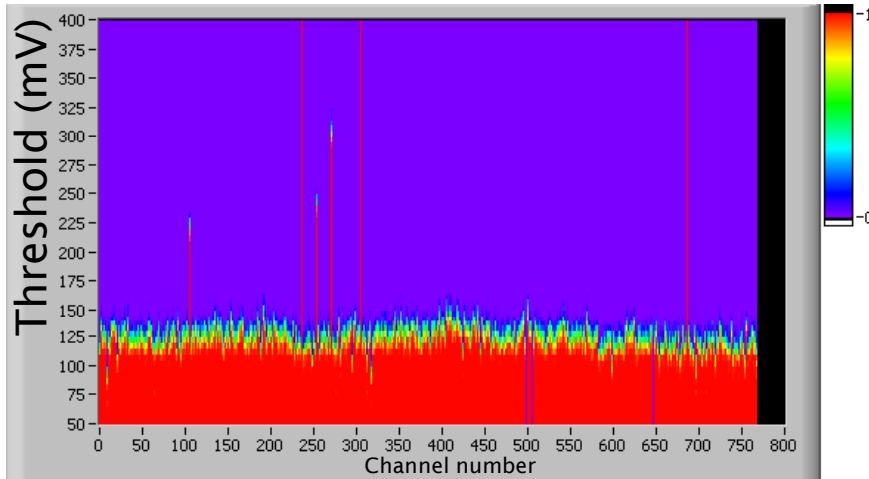
(ABCD, 800nm)

3) Stave07: 30 module stave with ABCD

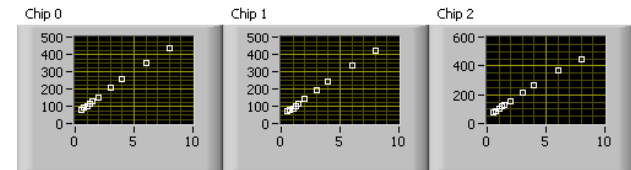


(Future: $24 * \sim 1V = 24V$ for 130nm ABCN)

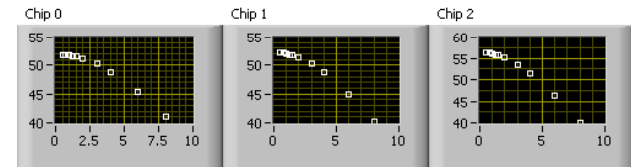
Thirty Module Stave: Some Results



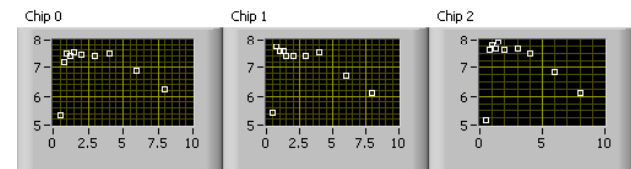
VT50
(mV)



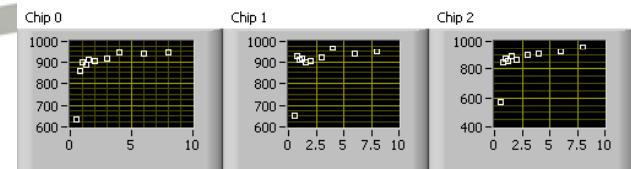
Gain
(mV/fC)



Output
Noise (mV)



Input
Noise (ENC)

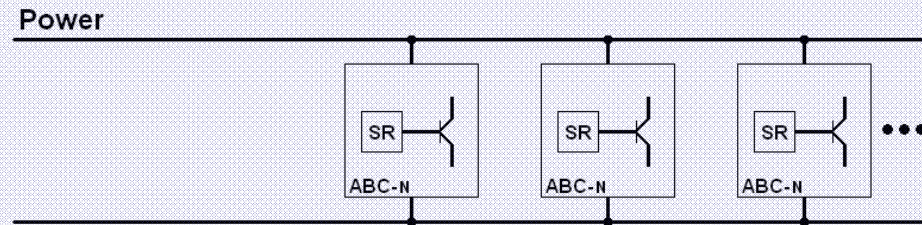


Shunt Regulator Architectures

- **Hybrid with Shunt “W”**

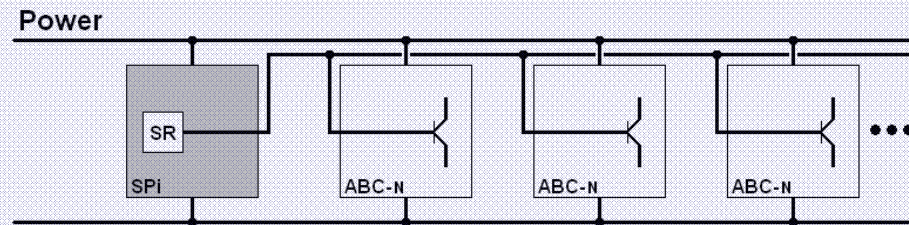
- Use each ABCN’s integrated shunt regulator
- Use each ABCN’s integrated shunt transistor(s)

See “Serial power circuitry in the ABC-Next and FE-I4 chips” to be given this afternoon by W. Dabrowski



- **Hybrid with Shunt “M”**

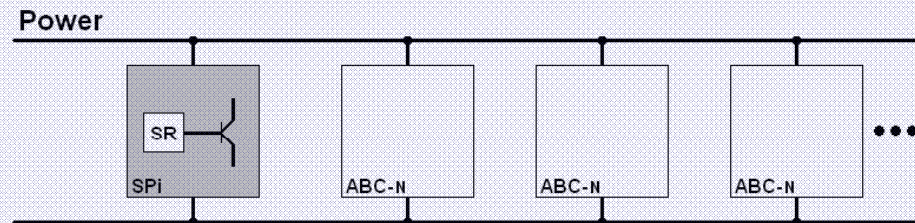
- Use one external shunt regulator
- Use each ABCN’s integrated shunt transistor(s)
 - Two (redundant) shunt transistors, 140mA each



- **Hybrid with SPi (or similar)**

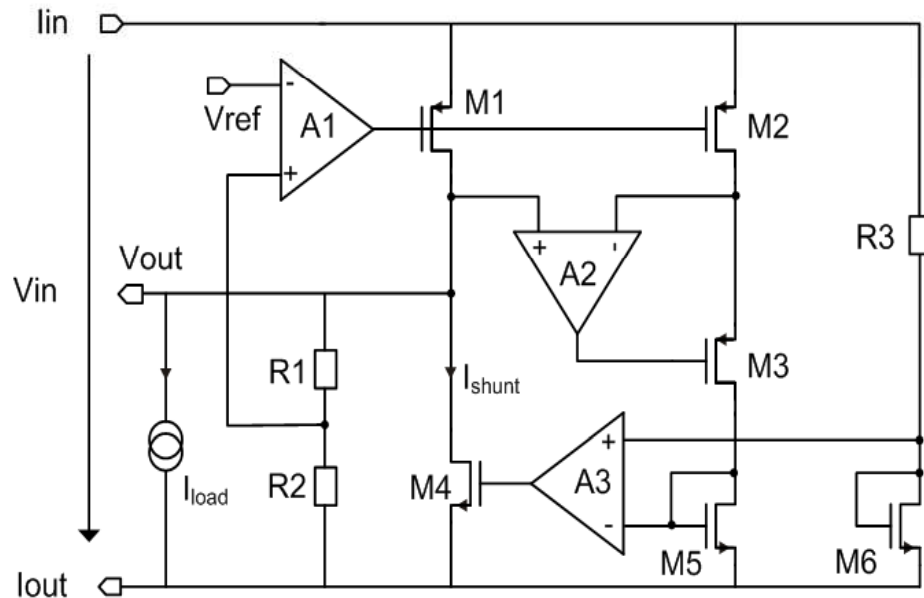
- Use one external shunt regulator
- Use one external power transistor

See “The Serial Power Interface Chip”, to be given this afternoon by M. Trimpl



Each option has its merits. All now available in silicon:
final choice to be based upon test results.

Simplified Schematic



- Combination of LDO and shunt transistor
- M4 shunts the current not drawn by the load
- Fraction of M1 current is mirrored & drained into M5
- Amplifier A2 & M3 improve mirroring accuracy
- Ref. current defined by resistor R3 & drained into M6
- Comparison of M5 and ref. current leads to constant current flow in M1
- Ref. current depends on voltage drop V_{lin} which again depends on supply current I_{in}

- „Shunt-LDO“ regulators having completely different output voltages **can be placed in parallel** without any problem regarding mismatch & shunt current distribution
- Resistor R3 mismatch will lead to some variation of shunt current (10-20%)
- „Shunt-LDO“ **can cope with an increased supply current** if one FE-I4 does not contribute to shunt current e.g. disconnected wirebond → ref current goes up
- Can be used as an **ordinary LDO when shunt is disabled**

Power Requirements with Modern Process Technologies

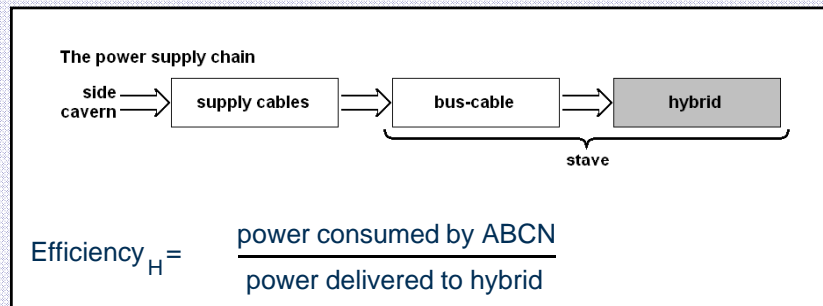
					Power per 128 channel chip	per channel
In ATLAS SCT	ABCD (0.8µm, biCMOS)	Digital: 4.0 volts Analogue: 3.5 volts	35 mA per chip (actual) 74 mA per chip (actual)	=> 4.0 x 35 + 3.5 x 74 = 399 mW		3.1 mW
Present Prototype	ABCN25 (0.25µm CMOS)	Digital: 2.5 volts Analogue: 2.2 volts	95 mA per chip (preliminary) 27 mA per chip (preliminary)	=> 2.5 x 95 + 2.2 x 27 = 300 mW		2.3 mW
Proposed	ABCN13 (0.13µm CMOS)	Digital: 0.9 volts Analogue: 1.2 volts	**51 mA per chip (estimate) **16 mA per chip (estimate)	=> 0.9 x 51 + 1.2 x 16 = 65 mW		0.5 mW

<p>ABCN25: $V_{dig} > V_{ana}$ $I_{dig} \gg I_{ana}$</p> <p>If we generate V_{ana} from V_{dig} using LR:</p> <ul style="list-style-type: none"> • $27\text{mA} * 0.3\text{V} = 8.1\text{mW}$ per chip • 3% of chip power 	<p>ABCN13: $V_{ana} > V_{dig}$ $I_{dig} \gg I_{ana}$</p> <p>If we generate V_{dig} from V_{ana} using LR:</p> <ul style="list-style-type: none"> • $95\text{mA} * 0.3\text{V} = 28.5\text{mW}$ per chip • 44% of chip power • Can we do better than this? <i>Of course...</i>
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** Power Estimates for an ABCN in 130nm Technology, Mitch Newcomer, Atlas Tracking Upgrade workshop, NIKHEF, November 2008
<http://indico.cern.ch/getFile.py/access?contribId=16&sessionId=8&resId=0&materialId=slides&confId=32084>

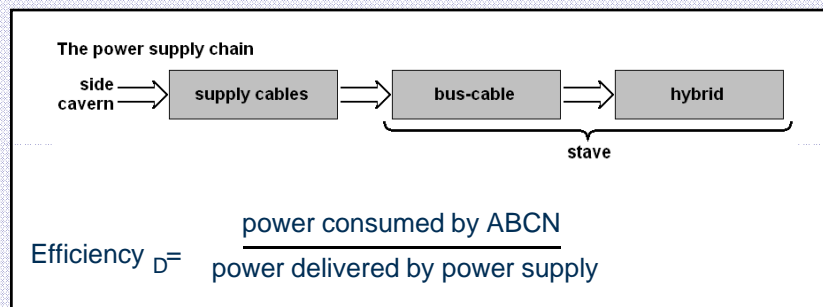
Efficiency - definitions

Definition – Hybrid (excludes stave interconnects & supply cables)



Efficiency_H

Definition – Detector (includes all supply cables)



Efficiency_D

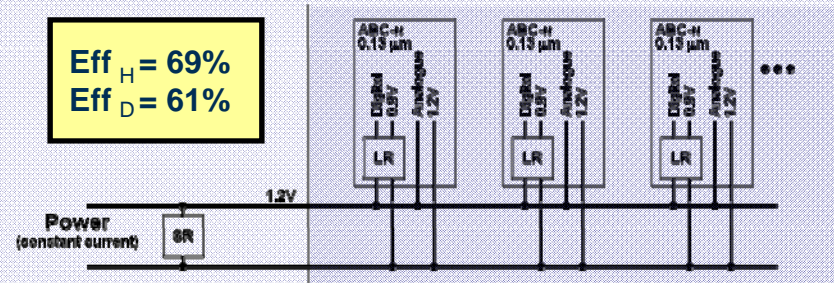
Some assumptions: Cable resistance 2 ohms for each line pair, SR = 85%, low current DC-DC = 90%, high current DC-DC = 85%

ABCN demand power is dependant on task. This will normally mean a shunt regulator will dissipate some power to maintain voltage under all conditions.

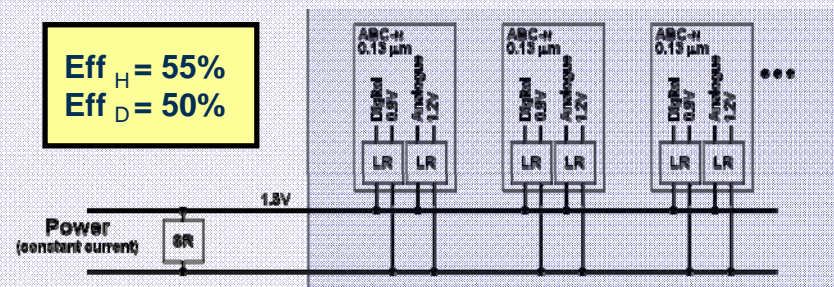


Favoured SP Options

Low Noise:
On-chip Linear Regulator
for Digital only



Very Low Noise:
On-chip Linear Regulators
for both Analogue and Digital



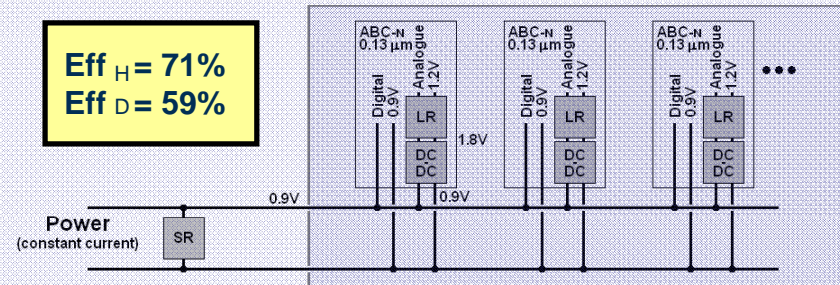
For further details, see this afternoon's presentation by W. Dabrowski:
"Serial power circuitry in the ABC-Next and FE-I4 chips"

Favoured SP Options

Also Low Noise:

Analogue from on-chip DC-DC step using switched capacitors *and* linear regulator

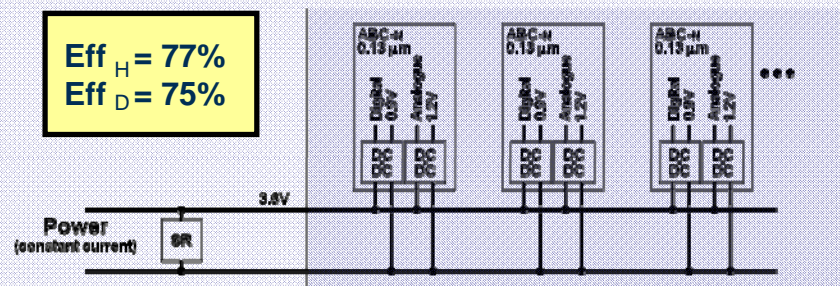
$\text{Eff}_H = 71\%$
 $\text{Eff}_D = 59\%$



Highest Efficiency:

“On-chip” DC-DC conversion using switched capacitors

$\text{Eff}_H = 77\%$
 $\text{Eff}_D = 75\%$



For further details, see this afternoon’s presentation by W. Dabrowski:
“Serial power circuitry in the ABC-Next and FE-I4 chips”

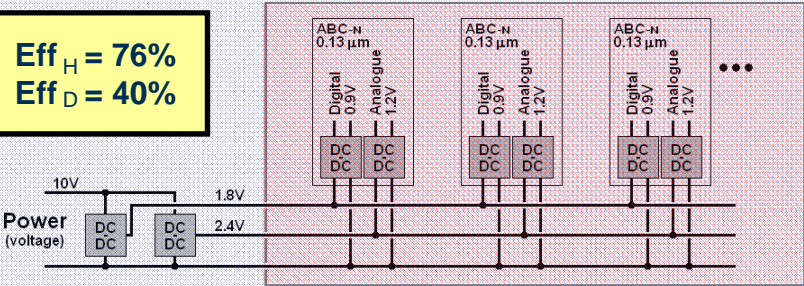
For the sake of Comparison...

Off-chip DC-DC conversion
from 10V to 2.4V and 1.8V
(assume 85% efficiency)

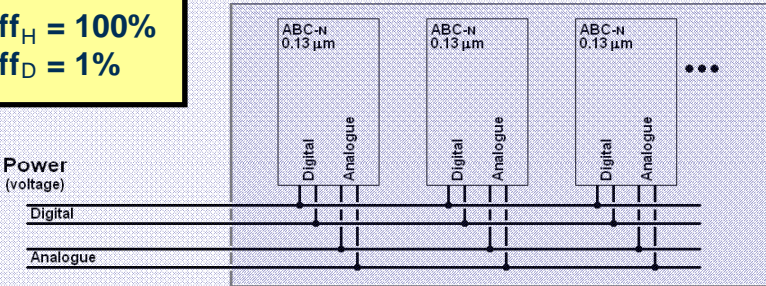
“On-chip” DC-DC conversion
using switched capacitors
(assume 90% efficiency)

Independent Power

$Eff_H = 76\%$
 $Eff_D = 40\%$



$Eff_H = 100\%$
 $Eff_D = 1\%$

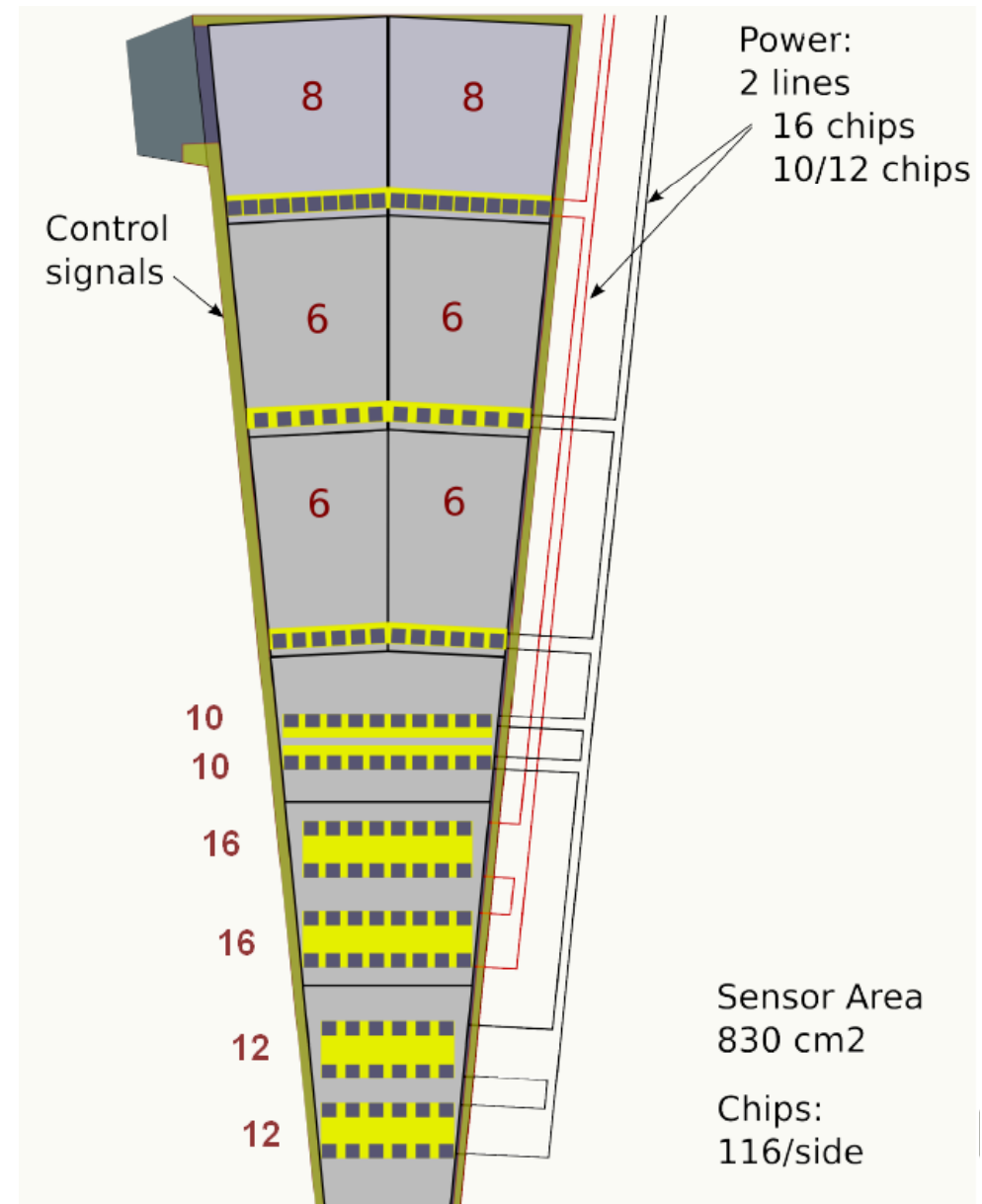


With ABCN in 130 nm technology, we shall study several options to obtain the best balance between efficiency and performance...

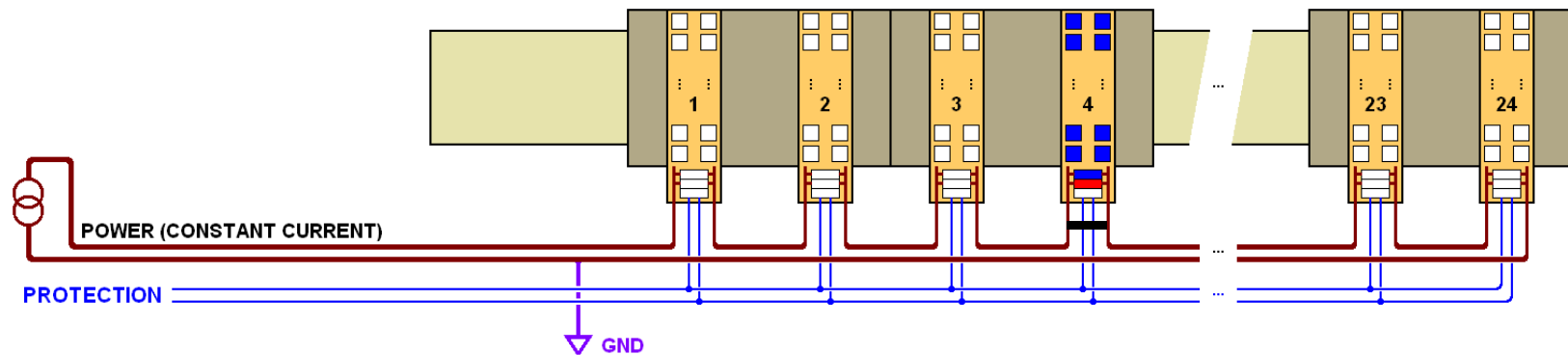
SP and Endcap Geometries

The baseline design for the endcap of an upgraded ATLAS strip detector is based around petals.

- **Not all hybrids have the same number of chips**
 - Group hybrids with *similar* numbers of chips into their own power chains
- Chain 1: (3*16) chip units
- Chain 2: (4*12)+(2*10) chip units
 - Additional current corresponding to two chips must be dissipated by the shunt(s) on each 10 chip hybrid.
- Efficiency depends upon the values of the analogue and digital voltages and the means used to generate them:
 - Example: 3 ohm cable pair, 1.5V supply, 140mA per chip and 85% shunt efficiency => **54% efficiency**
 - **GOOD ENOUGH**



Protection



Whilst demonstration staves have generally been reliable:

- What happens if a module fails open circuit?
- What happens if a module becomes a noise generator?

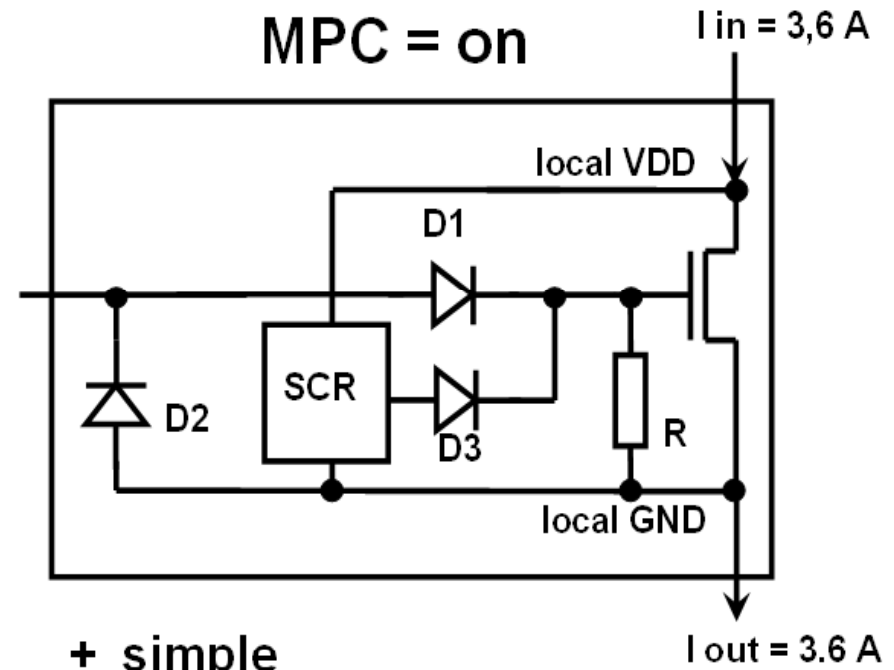
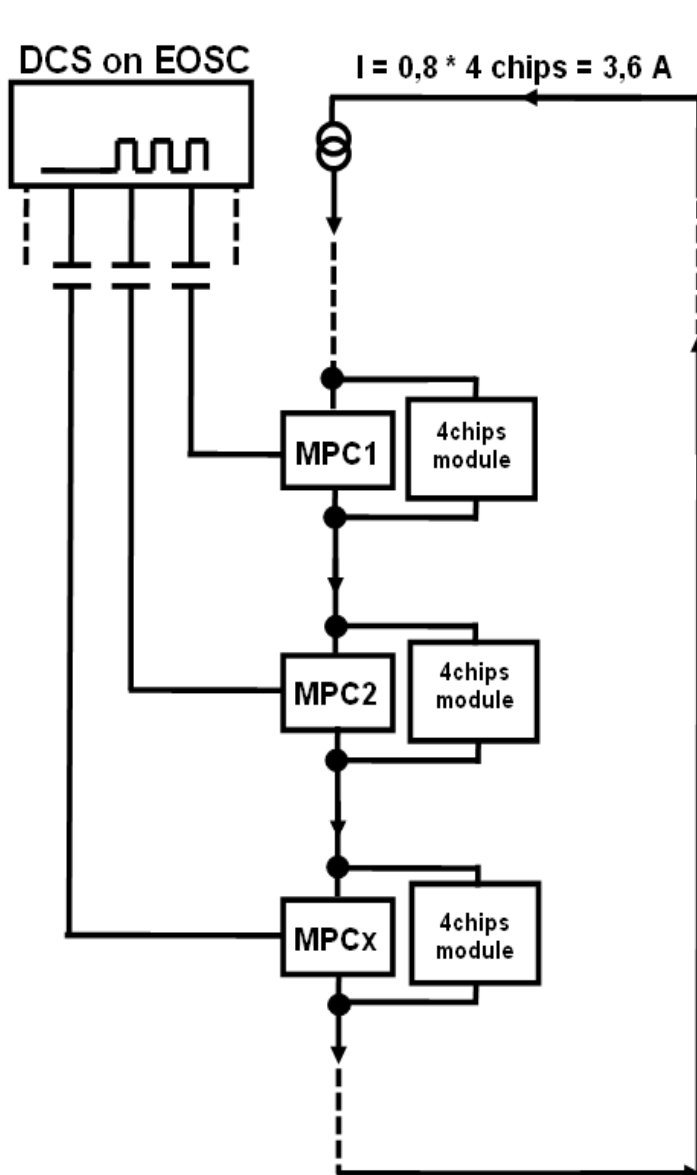
We could provide a system to “short out” each module under control of DCS

- Voltage across shorted module should be small ($<100\text{mV}$)
- Area of components and number of control lines must be small
- Automatic over current and over voltage protection is desirable
- Protection circuit must draw no (minimal) power when module active
- Ability to put modules into “stand by” (low power state)

See poster by Richard Holt for details of proposals by Bonn, BNL and RAL

Bonn Scheme: Module Protection Chip

“Serial Powering Protection”, Andreas Eyring, ATLAS Upgrade Week, CERN, Feb 2008
<http://indico.cern.ch/materialDisplay.py?contribId=4&materialId=slides&confId=52375>



- + simple
 - + control & monitor
 - + fast auto-response
- default state = OC

OC = Open Circuit (ie switch is “off”, module powered)

- 1 AWG 36 line / module

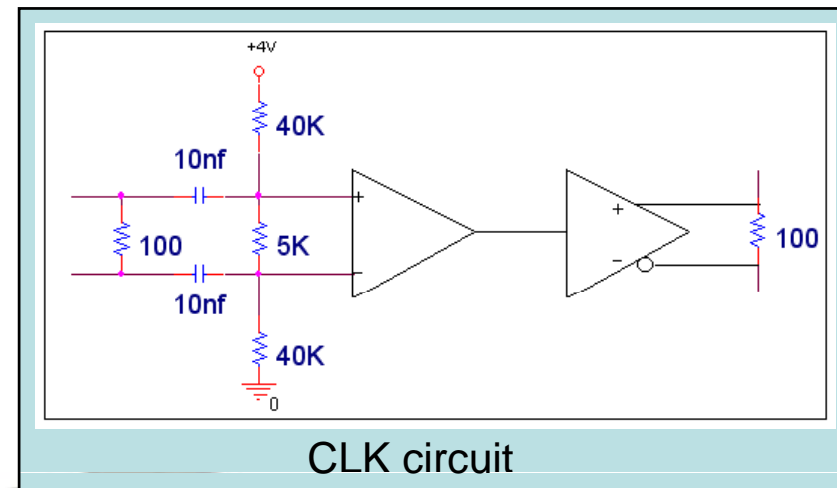
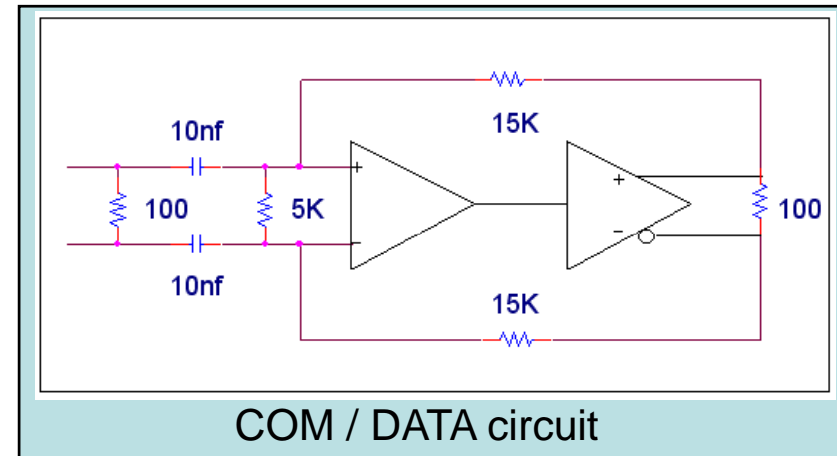
BNL and RAL are addressable schemes (fewer lines)

Silicon prototype by Summer/Autumn 2009

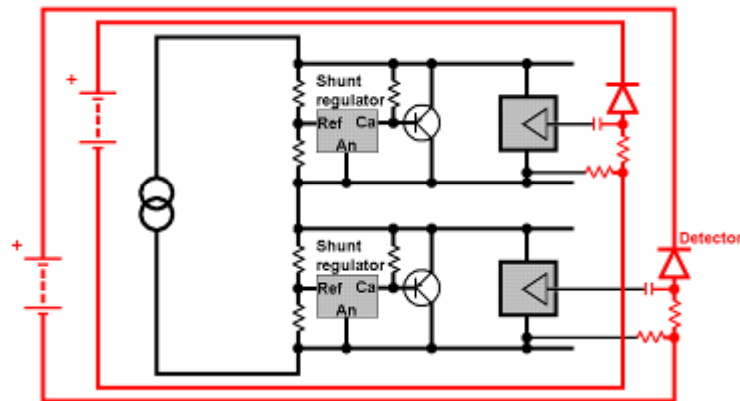
AC Coupled (M)LVDS Receivers

A viable solution!

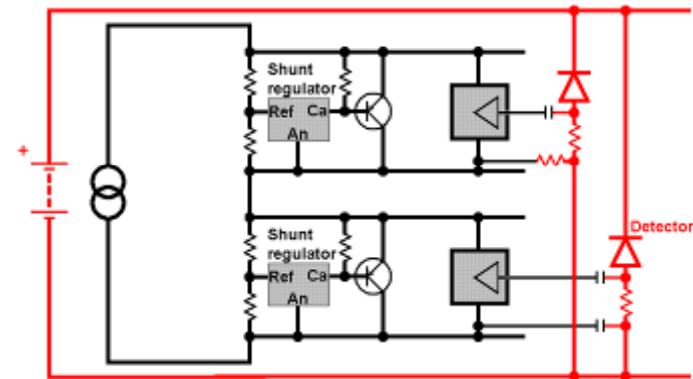
- No need for DC balanced codes
 - COM/DATA circuit could be simplified if DC balanced codes were used (DC balanced remains the baseline for production staves)
- All components apart from the capacitors can be integrated into custom chips
 - Capacitors need to be rated to ~30V, more for present prototypes
- MLVDS drivers offers higher currents and MLVDS receivers lower thresholds (than LVDS)
 - Can help increase margins
- **Working well on STAVE07**



Serial Powering and HV



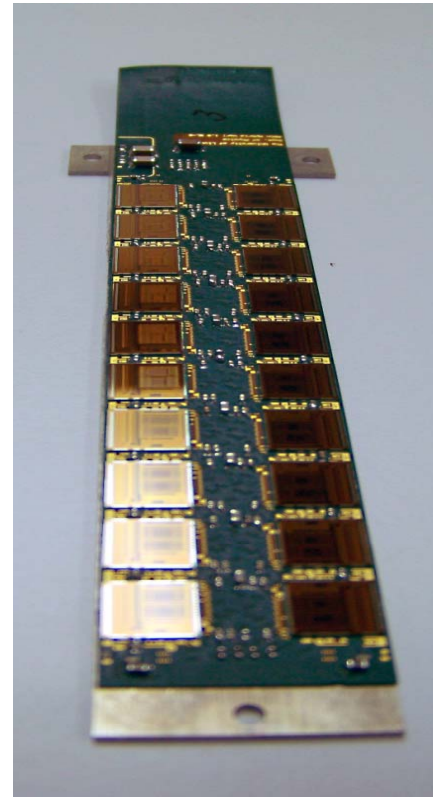
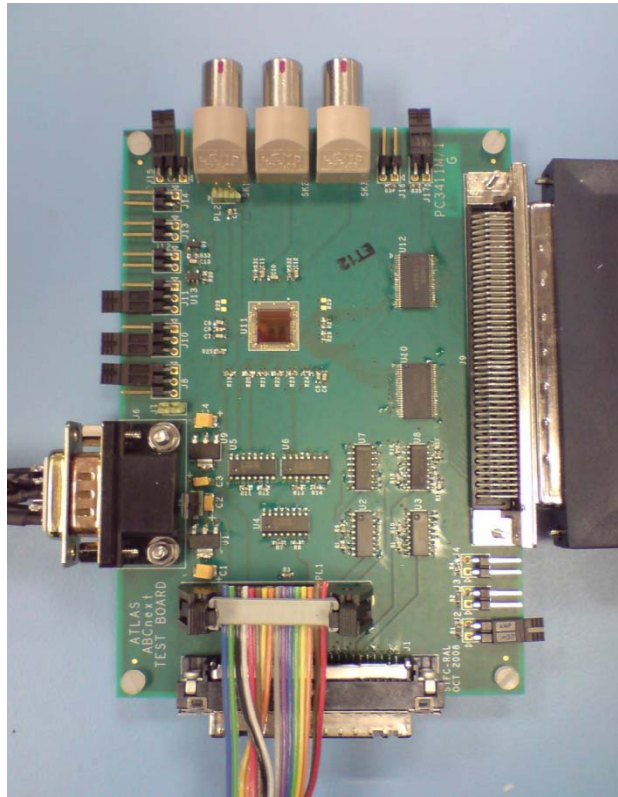
Standard HV powering: one HV per module



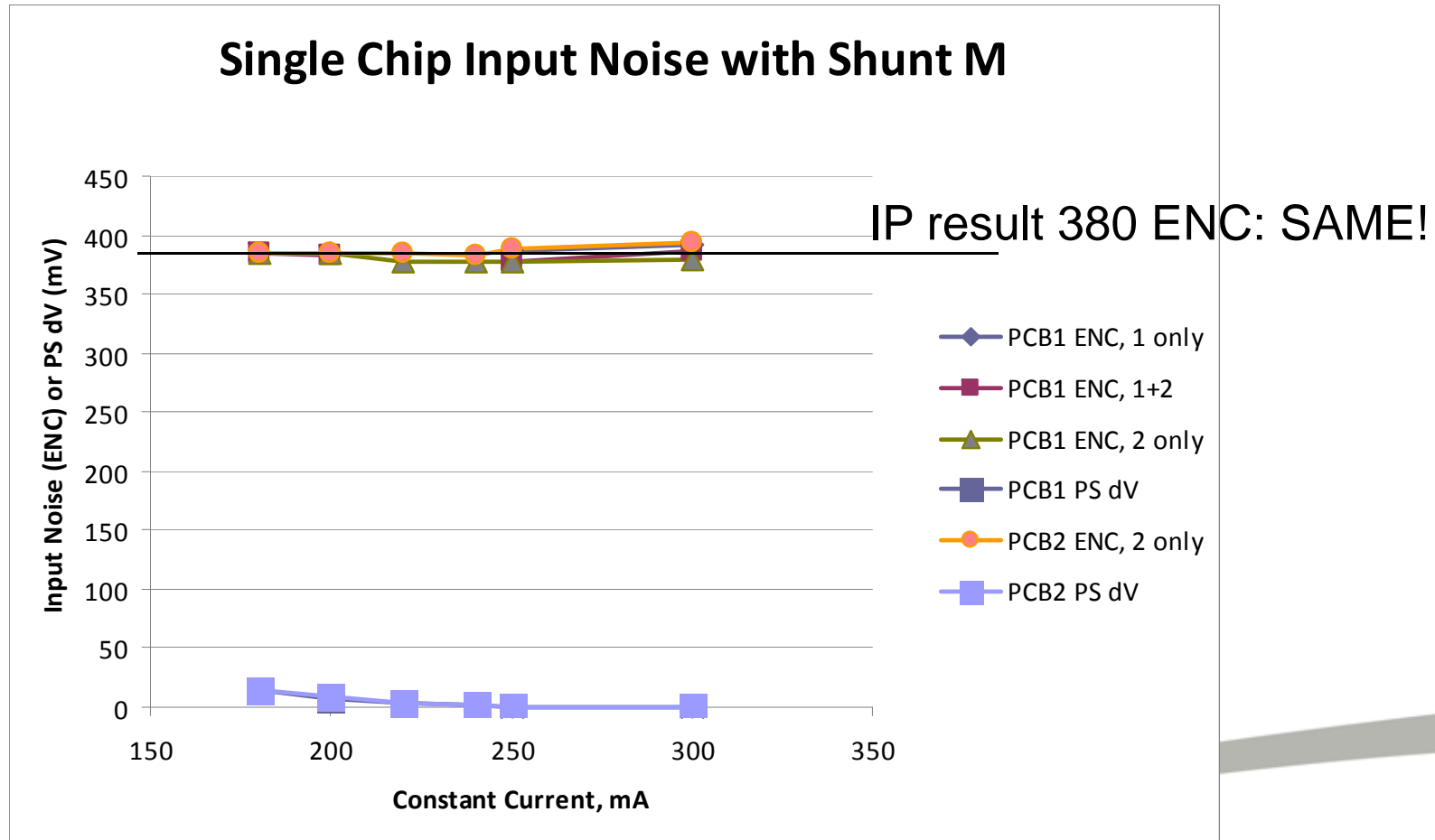
Alternative HV powering: one HV supply per M modules

- Serial Powering is compatible with the use of a single HV supply for several modules
- Each sensor is dynamically connected to current source ground through output impedances of the chain of shunt regulators
- Low shunt output impedance is crucial to achieve good 'grounding' and reduce noise

First tests of integrated shunts in ABCN: RAL single chip PCB and Liverpool Hybrid

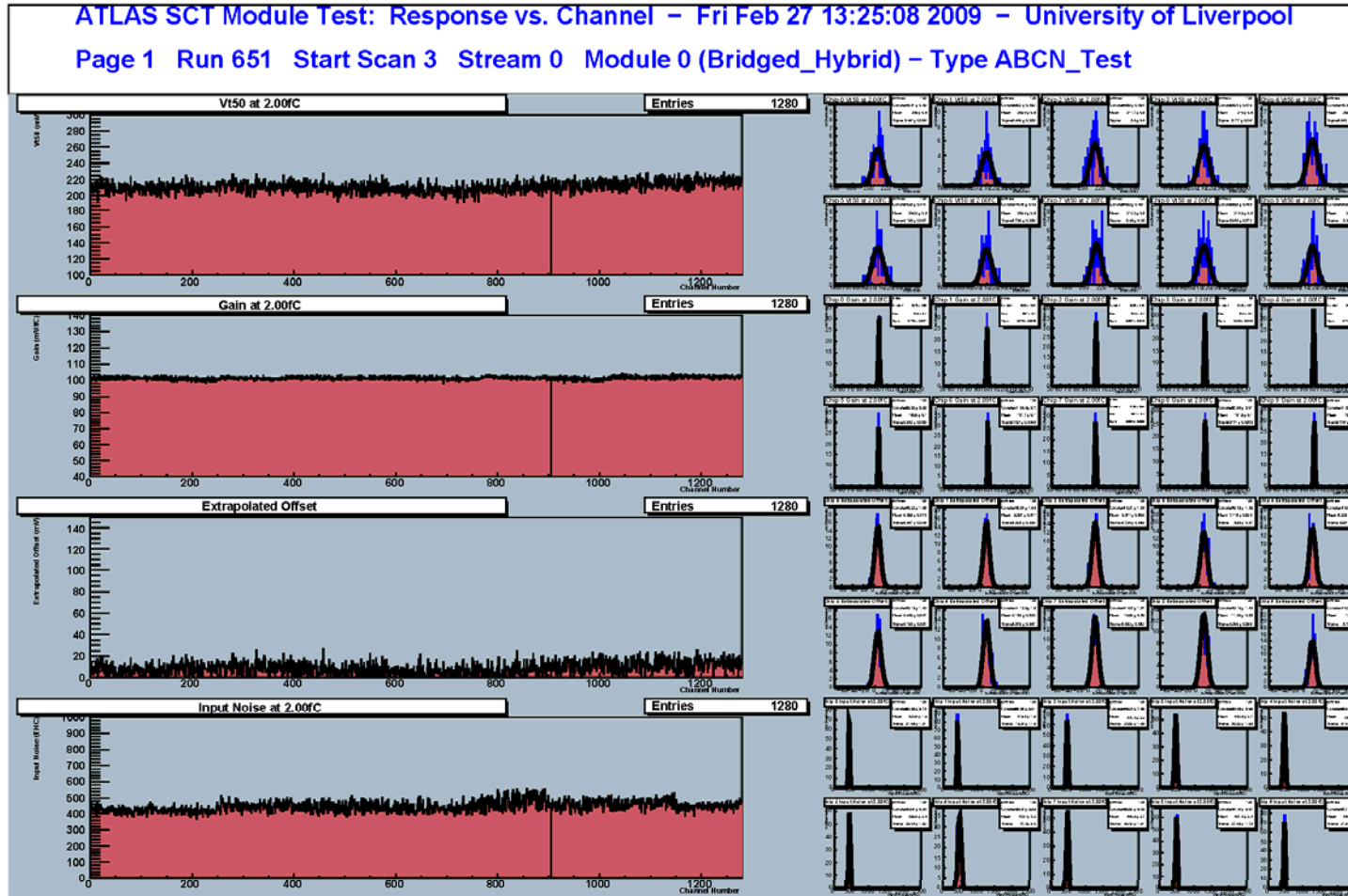


Single Chip using shunt “M”



ABCN hybrid using shunt "W"

PRELIMINARY





SP Summary and Next Steps

- We have ~2 years successful experience building and running staves with commercial SP components
- Shunt circuitry can be integrated into FE chips
 - Low requirements in terms of component area
 - First results from ABCN shunts very encouraging
- Protection can be part of SP architecture
 - Basic scheme demonstrated
- First ABCN demonstrator staffe planned for this year
 - Integrated shunts + protection
- SP is an attractive option for sLHC power distribution!

Supplemental Material



Large Diameter Wire Bonds



Delvotec 64/66000
100 – 600 micron wire

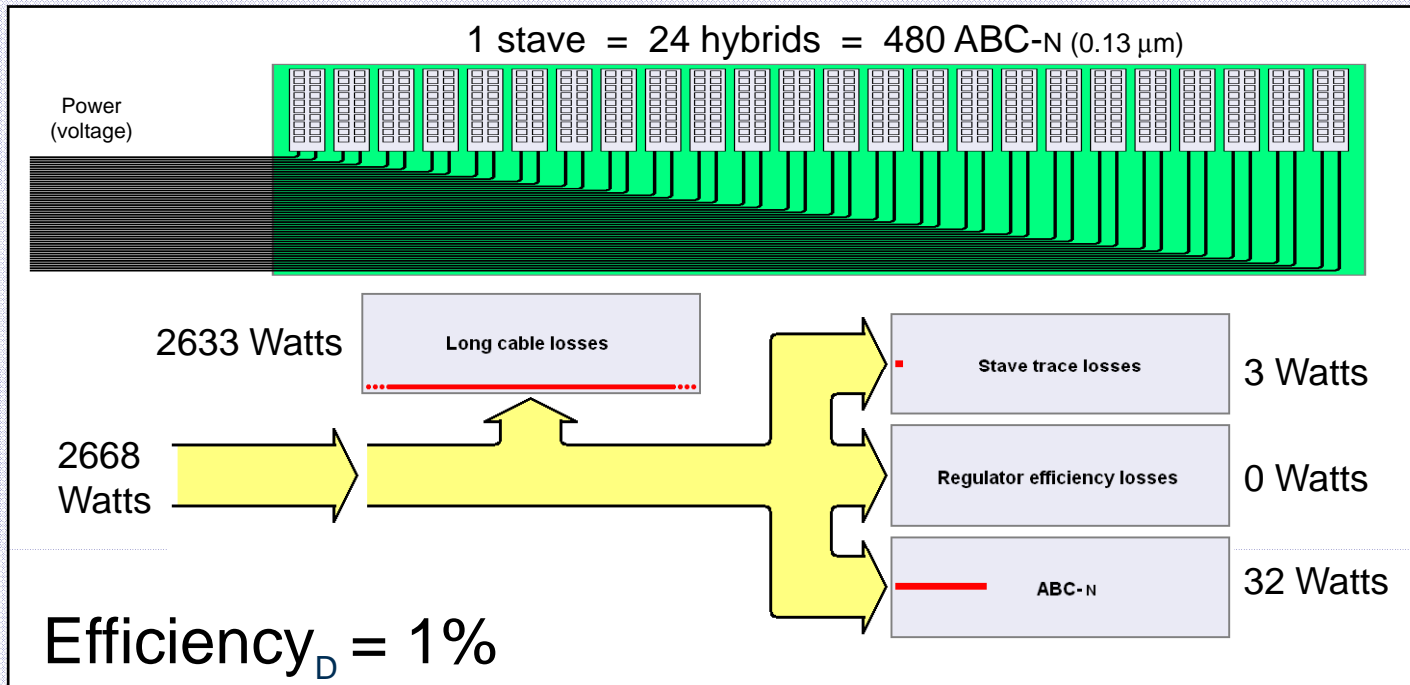
Used in harsh automotive applications, e.g. ABS
Shear strength for 250 micron bond 1000cN
250 micron bond => 15 A
Manufacturers can do test samples



Hesse + Knipps Bondjet BJ920
125 – 500 micron wire

Detector power efficiency

Independent powering (100% hybrid efficiency)



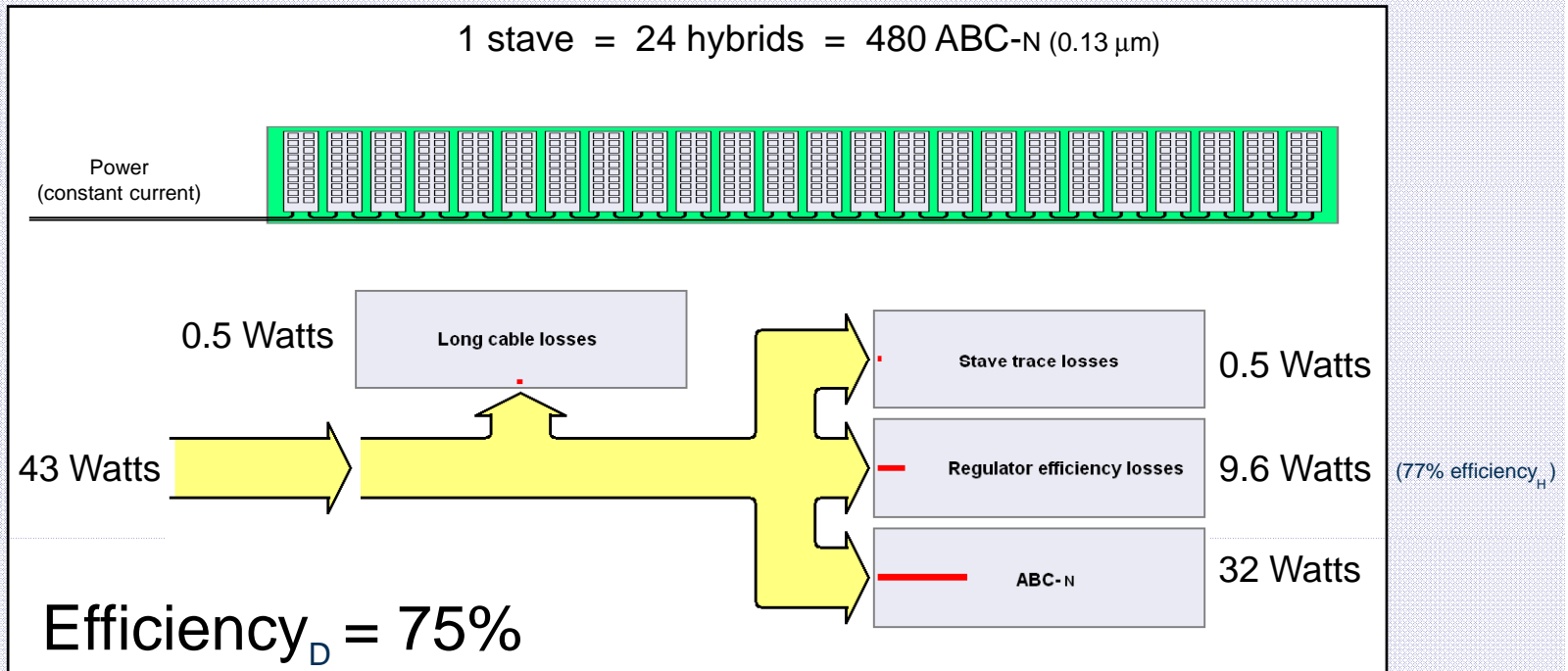
Independent supplies (line pairs) for digital and analogue power.

Same amount of copper => Cables are 96 ohms total for each line pair.
Each line pair carries 20 x 51mA (digital) and 20 x 16mA (analogue).

Numbers rounded

Detector power efficiency

Serial powering 3.6V, 3:1 & 4:1 DC-DC using switched capacitors



Cables assumed to be 2 ohms total for each power line pair

Regulator power = $(1/\text{eff}_H - 1) \times \text{ABC power}$

Stave supply current = $(32 + 9.6 + 0.5)\text{watts} / (3.6\text{volts} \times 24)$
 = 0.49amps

Numbers rounded

